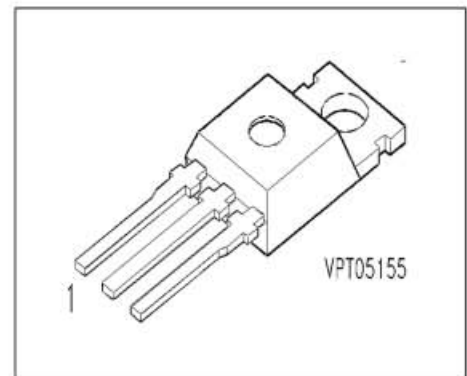


SIPMOS® Power Transistor

- N channel
- Enhancement mode
- Avalanche-rated



Pin 1	Pin 2	Pin 3
G	D	S

Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Ordering Code
BUZ 80 A	800 V	3.6 A	3 Ω	TO-220 AB	C67078-S1309-A3

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current $T_C = 26\text{ }^\circ\text{C}$	I_D	3.6	A
Pulsed drain current $T_C = 25\text{ }^\circ\text{C}$	I_{Dpuls}	14.5	
Avalanche current, limited by T_{jmax}	I_{AR}	3.1	
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	8	mJ
Avalanche energy, single pulse $I_D = 3.1\text{ A}$, $V_{DD} = 50\text{ V}$, $R_{GS} = 25\text{ }\Omega$ $L = 62.4\text{ mH}$, $T_j = 25\text{ }^\circ\text{C}$	E_{AS}	320	
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_C = 25\text{ }^\circ\text{C}$	P_{tot}	100	W
Operating temperature	T_j	-55 ... + 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip case	R_{thJC}	≤ 1.25	K/W
Thermal resistance, chip to ambient	R_{thJA}	75	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	